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November 2013

# **FDP24N40**

# N-Channel UniFET<sup>TM</sup> MOSFET 400 V, 24 A, 175 m $\Omega$

#### **Features**

- $R_{DS(on)}$  = 140 m $\Omega$  (Typ.) @  $V_{GS}$  = 10 V,  $I_D$  = 12 A
- Low Gate Charge (Typ. 46 nC)
- Low C<sub>rss</sub> (Typ. 25 pF)
- 100% Avalanche Tested
- RoHS Compliant

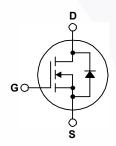
# **Applications**

- · Uninterruptible Power Supply
- AC-DC Power Supply

# **Description**

UniFET<sup>TM</sup> MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





# **MOSFET Maximum Ratings** $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol		Parameter		FDP24N40	Unit	
$V_{DSS}$	Drain to Source Voltage			400	V	
V <sub>GSS</sub>	Gate to Source Voltage			±30	V	
	Drain Current	- Continuous (T <sub>C</sub> = 25°C)		24	_	
ID	Diamounent	- Continuous (T <sub>C</sub> = 100°C)		14.4	Α	
I <sub>DM</sub>	Drain Current	- Pulsed	(Note 1)	96	Α	
E <sub>AS</sub>	Single Pulsed Avalanch	e Energy	(Note 2)	1296	mJ	
I <sub>AR</sub>	Avalanche Current		(Note 1)	24	Α	
E <sub>AR</sub>	Repetitive Avalanche E	nergy	(Note 1)	22.7	mJ	
dv/dt	Peak Diode Recovery d	v/dt	(Note 3)	4.5	V/ns	
c	Dower Dissination	(T <sub>C</sub> = 25°C)		227	W	
$P_{D}$	Power Dissipation	- Derate Above 25°C		1.8	W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage	Temperature Range		-55 to +150	°C	
T <sub>L</sub>	Maximum Lead Temper	ature for Soldering, 1/8" from Case for 5 Sec	conds	300	οС	

### **Thermal Characteristics**

Syı	mbol	Parameter	FDP24N40	Unit
$R_{\thetaJC}$		Thermal Resistance, Junction to Case, Max.	0.55	°C/W
$R_{\theta JA}$		Thermal Resistance, Junction to Ambient, Max. 62.5		- 0/00

# **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDP24N40	FDP24N40	TO-220	Tube	N/A	N/A	50 units

# **Electrical Characteristics** $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V, T_J = 25^{\circ} C$	400	-	-	V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, Referenced to 25°C	-	0.4	-	V/°C
1	Zero Gate Voltage Drain Current	$V_{DS} = 400 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	μА
IDSS	Zero Gate voltage Drain Current	$V_{DS} = 320 \text{ V}, T_{C} = 125^{\circ}\text{C}$	-	-	10	μΑ
$I_{GSS}$	Gate to Body Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	±100	nA

#### **On Characteristics**

V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu\text{A}$	3.0	-	5.0	V
R <sub>DS(on)</sub>	Static Drain to Source On Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 12 A	-	0.140	0.175	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 20 V, I <sub>D</sub> = 12 A	-	34	-	S

# **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V 05 V V 0 V		-	2270	3020	pF
C <sub>oss</sub>	Output Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1 MHz		-	365	490	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - 1 1/11/12		-\	25	38	pF
Q <sub>g(tot)</sub>	Total Gate Charge at 10V	V <sub>DS</sub> = 320 V, I <sub>D</sub> = 24 A,		- \	46	60	nC
Q <sub>gs</sub>	Gate to Source Gate Charge	V <sub>GS</sub> = 10 V		- \	12	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge	(N	ote 4)	-	20	-	nC

# **Switching Characteristics**

	9						
t <sub>d(on)</sub>	Turn-On Delay Time			-	40	90	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{DD} = 200 \text{ V}, I_D = 24 \text{ A},$		-	90	190	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{GS}$ = 10 V, $R_G$ = 25 $\Omega$		-	110	230	ns
t <sub>f</sub>	Turn-Off Fall Time		(Note 4)	-	65	140	ns

#### **Drain-Source Diode Characteristics**

IS	Maximum Continuous Drain to Source Dioc	Maximum Continuous Drain to Source Diode Forward Current		-	24	Α
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Fo	orward Current	4 -	-	96	Α
$V_{SD}$	Drain to Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 24 A	-	-	1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 24 A,	-	360	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> /dt = 100 A/μs	-	4.7	-	μС

#### Notes

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. L = 4.5 mH, I<sub>AS</sub> = 24 A, V<sub>DD</sub> = 50 V, R<sub>G</sub> = 25  $\Omega$ , starting T<sub>J</sub> = 25°C.
- 3. I  $_{SD} \leq$  24 A, di/dt  $\leq$  200 A/µs, V  $_{DD} \leq$  BV  $_{DSS},$  starting T  $_{J}$  = 25°C.
- 4. Essentially independent of operating temperature typical characteristics.

# **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

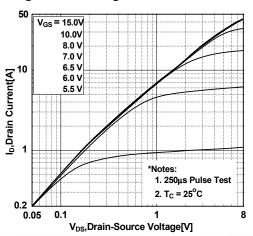


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

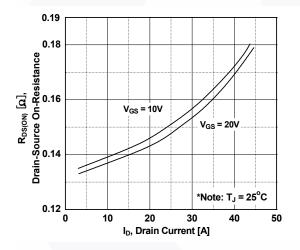


Figure 5. Capacitance Characteristics

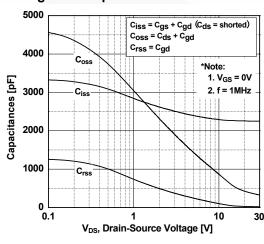


Figure 2. Transfer Characteristics

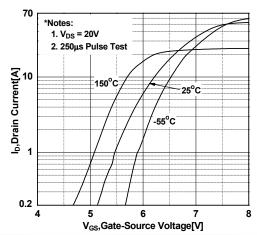


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

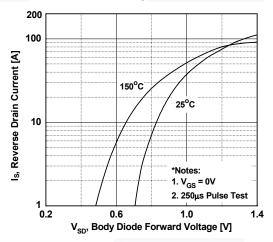
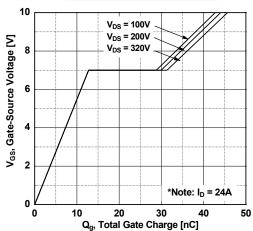


Figure 6. Gate Charge Characteristics



# **Typical Performance Characteristics** (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

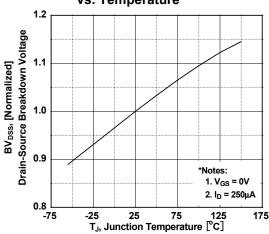


Figure 8. On-Resistance Variation vs. Temperature

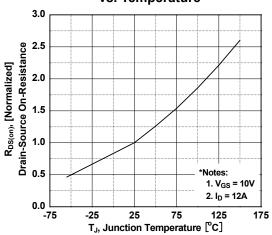


Figure 9. Maximum Safe Operating Area

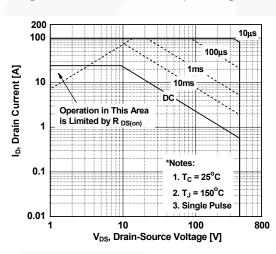


Figure 10. Maximum Drain Current vs. Case Temperature

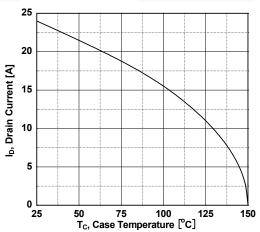
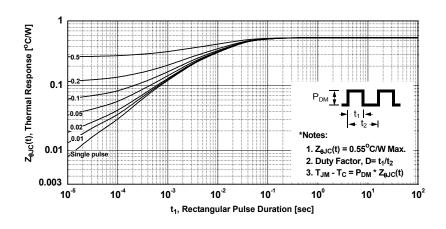


Figure 11. Transient Thermal Response Curve



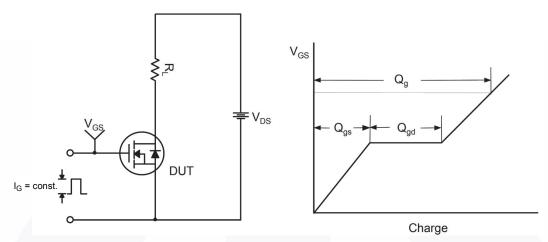


Figure 12. Gate Charge Test Circuit & Waveform



Figure 13. Resistive Switching Test Circuit & Waveforms



Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

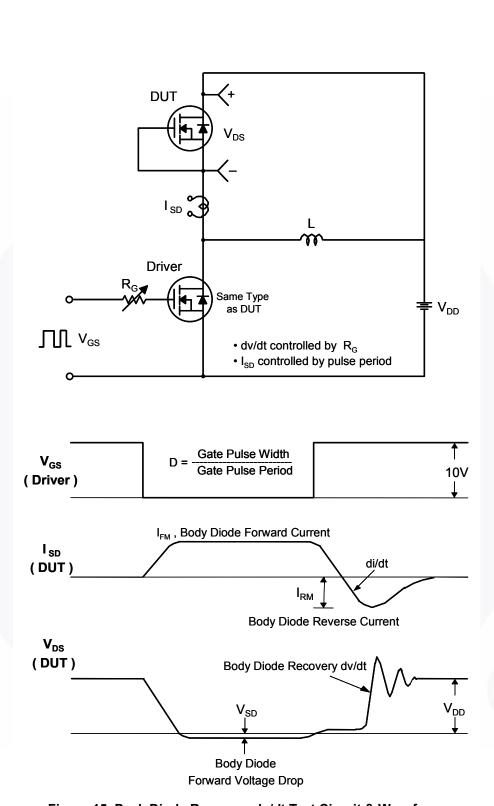


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

## **Mechanical Dimensions**

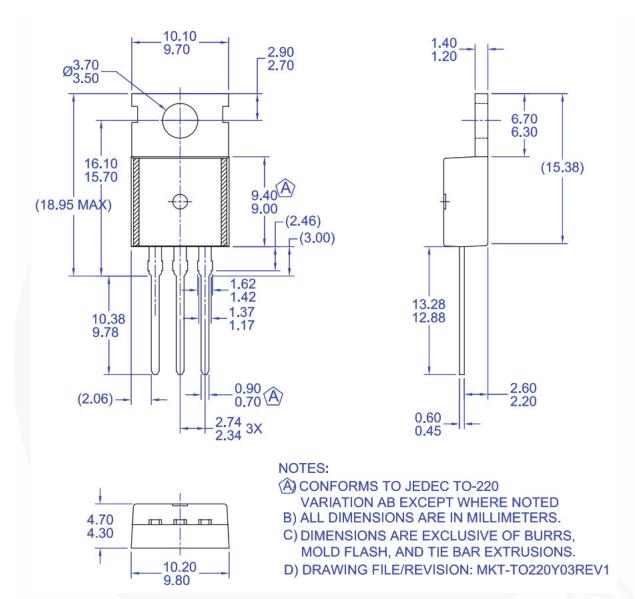


Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

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